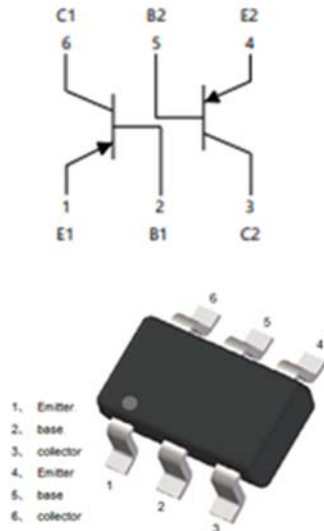


Dual PNP Small Signal Transistor



Features

- Moisture sensitivity level 1
- Halogen free and RoHS compliant
- Surface mount package ideally suited for automatic insertion

Application

- Signal amplification
- Switching circuit

Mechanical data

- **Package:** SOT-363S
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102

■ Maximum Ratings ($T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Conditions	Value
Device marking code				5Ft
Collector-base voltage	V_{CBO}	V	$I_C = -10\mu\text{A}, I_E = 0$	-80
Collector-emitter voltage	V_{CEO}	V	$I_C = -10\text{mA}, I_B = 0$	-65
Emitter-base voltage	V_{EBO}	V	$I_E = -10\mu\text{A}, I_C = 0$	-5
Collector current	I_C	mA		-100
Power dissipation	P_D	mW		200
Operation junction temperature	T_J	$^\circ\text{C}$		-55 to +150
Storage temperature	T_{STG}	$^\circ\text{C}$		-55 to +150



BC856BSS

RoHS
COMPLIANT

■ Electrical Characteristics (T_a=25°C Unless otherwise specified)

Item	Symbol	Unit	Conditions	Min	Typ	Max
Collector-base breakdown voltage	V _{(BR)CBO}	V	I _C =-10μA, I _E =0	-80		
Collector-emitter breakdown voltage	V _{(BR)CEO}	V	I _C =-10mA, I _B =0	-65		
Emitter-base breakdown voltage	V _{(BR)EBO}	V	I _E =-10μA, I _C =0	-5		
Collector cut-off current	I _{CBO}	nA	V _{CE} =-30V, I _B =0			-15
Emitter-base cutoff current	I _{EBO}	nA	V _{EB} =-5V, I _C =0			-100
DC current gain	h _{FE}		V _{CE} =-5V, I _C =-2mA	200		450
Collector-emitter saturation voltage	V _{CE(sat)1}	V	I _C =-10mA, I _B =-0.5mA			-0.3
	V _{CE(sat)2}	V	I _C =-100mA, I _B =-5mA			-0.65
Base-emitter voltage	V _{BE1}	V	V _{CE} =-5V, I _C =-2mA	-0.6		-0.75
	V _{BE2}	V	V _{CE} =-5V, I _C =-10mA			-0.82
Transition frequency	f _T	MHz	V _{CE} =-5V, I _C =-10mA, f=100MHz	100		

■ Thermal Characteristics

Parameter	Symbol	Unit	Value
Thermal resistance, junction-to-ambient	R _{θJ-A} ⁽¹⁾	°C/W	625
Thermal resistance, junction-to-case	R _{θJ-C} ⁽¹⁾	°C/W	500

Note:

(1) Device mounted on PCB, single-sided copper, with standard footprint



■ Characteristics

Fig 1: Static Characteristics

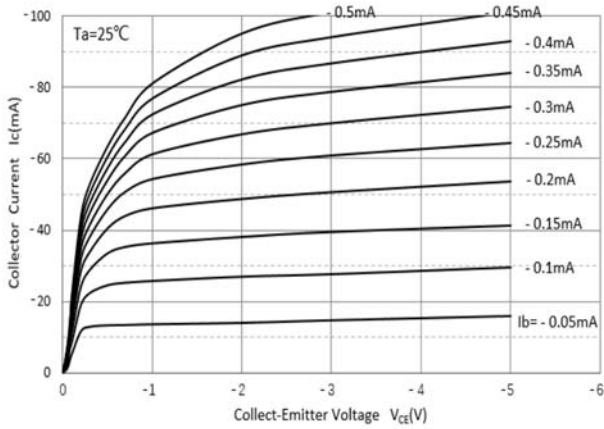


Fig 2: DC Current Gain Characteristics

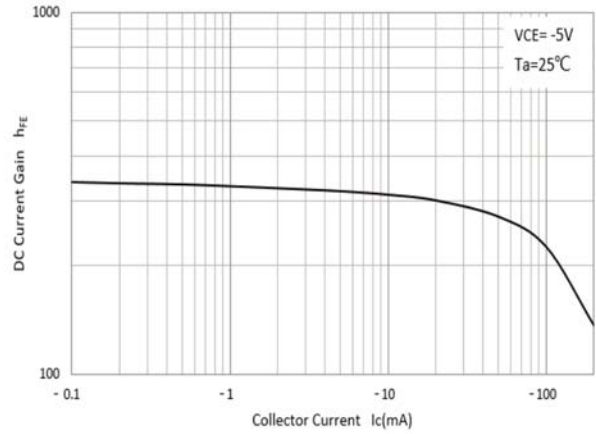


Fig 3: Collector-Emitter Saturation Voltage

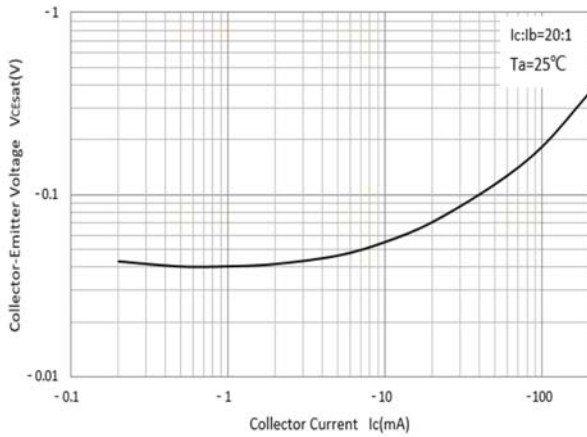


Fig 4: Base-Emitter Saturation Voltage

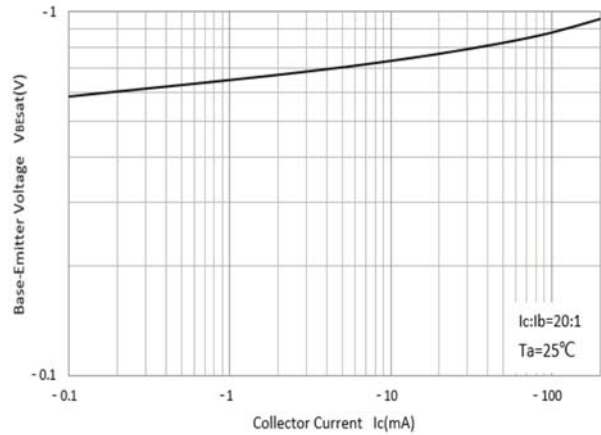


Fig 5: Base-emitter on voltage

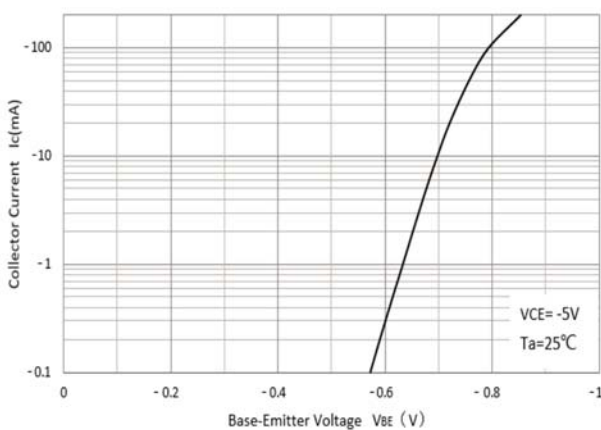


Fig 6: Cob/Cib- V_{CB}/V_{EB}

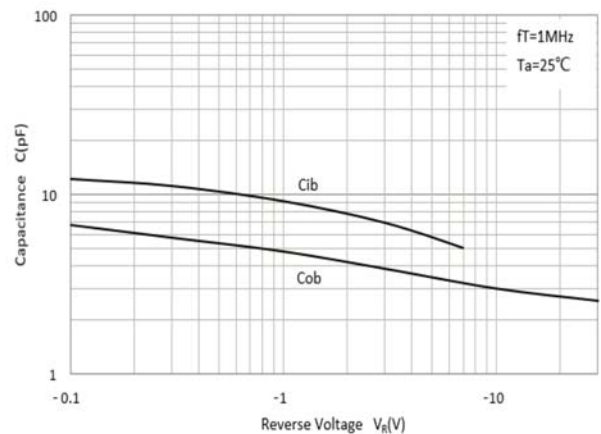
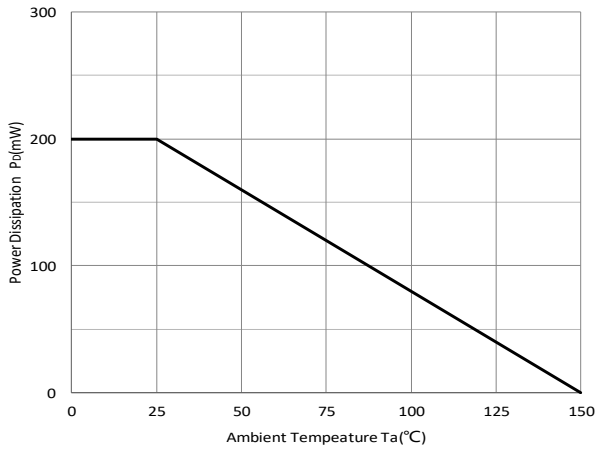




Fig 7: P_D-T_a Curve

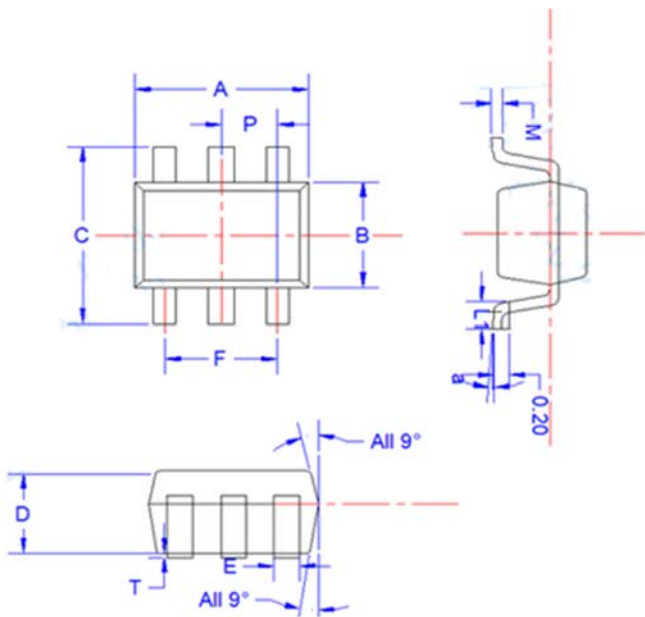




■ Ordering Information

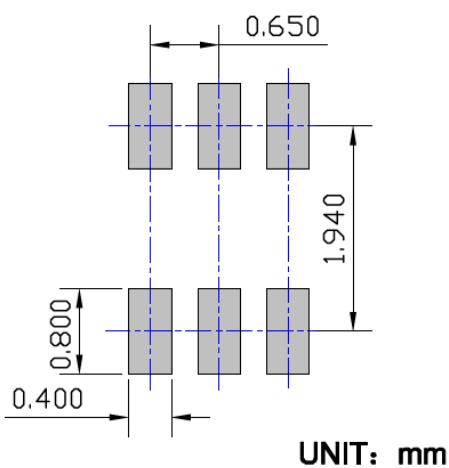
Preferred P/N	Packing Code	Unit weight(g)	Minimum package(pcs)	Inner box quantity(pcs)	Outer carton quantity(pcs)	Delivery mode
BC856BSS	F2	Approximate 0.009	3000	30000	120000	7" reel
BC856BSS	F3	Approximate 0.009	10000	/	210000	7" reel

■ Outline Dimensions



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
E	0.15	0.25	0.35
B	1.15	1.25	1.35
C	2.00	2.10	2.20
P	0.650BSC		
A	1.80	2.00	2.20
T	0.00	0.05	0.100
D	0.90	0.95	1.00
L1	0.20	0.30	0.40
α	4°±4°		
M	0.10	0.15	0.25

■ Suggested Pad Layout





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